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AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

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IN THE CLAIMS

Please amend the claims as follows:

1. (Previously presented) A process comprising:

first forming an imprinted first polymer disposed upon a printed wiring board (PWB) under conditions to increase the glass transition temperature (T_G) of the first polymer;

subsequently thermal curing an imprinted subsequent polymer disposed over the first polymer, and

in situ testing a board layout on the PWB while the PWB is attached as part of an array of not singulated PWBs.

2. (Original) The process of claim 1, before subsequently thermal curing, the process further including:

subsequently thermal imprinting the subsequent polymer, under conditions to increase the $T_{\rm G}$ of the second polymer.

- 3. (Original) The process of claim 1, wherein subsequently thermal curing includes a single thermal cure, selected from mircrowave radiation, infrared radiation, and convection.
- 4. (Previously presented) The process of claim 1, wherein first forming an imprinted first polymer exposes a portion of the PWB.
- 5. (Previously presented) The process of claim 1, wherein first forming an imprinted first polymer exposes a portion of the PWB to form a first topology, further including: forming a first metallization within a recess in the first topology.

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- 6. (Previously presented) The process of claim 1, wherein subsequently thermal curing is carried out under conditions to heat the subsequent polymer at a greater rate than the PWB.
- 7. (Previously presented) The process of claim 1, further including: first imprinting the first polymer to form a first topology, wherein first imprinting exposes a portion of the PWB; and

subsequently imprinting the subsequent polymer to form a second topology, wherein the second topology exposes a portion of the first polymer.

8. (Previously presented) The process of claim 1, further including: first imprinting the first polymer to form a first topology, wherein first imprinting exposes a portion of the PWB;

forming a first metallization within a recess in the first topology;

subsequently thermal imprinting the subsequent polymer to form a second topology, under conditions to increase the T_G of the second polymer, wherein the second topology exposes a portion of the first polymer; and

forming a subsequent metallization within a recess in the subsequent topology.

9. (Previously presented) The process of claim 1, wherein the PWB includes an upper surface and a lower surface, wherein the first polymer is disposed upon the upper surface, wherein the first polymer includes a cured polymer upper first film, wherein the subsequent polymer includes a cured polymer upper second film, and upon the lower surface, the process further including:

first thermal curing a lower first polymer under conditions to heat the lower first polymer at greater rate than the PWB; and

subsequently thermal curing an imprinted subsequent lower polymer disposed over the lower first polymer.

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- 10. (Previously presented) The process of claim 1, wherein the first polymer is formed over the PWB by depositing a prepolymer selected from a resin, a cyanate ester, a polyimide, a polybenzoxazole, a polybenzimidazole, a polybenzothiazole, and combinations thereof.
- 11. (Previously presented) The process of claim 1, wherein the first polymer includes a filmto-substrate thickness ratio selected from about one-tenth, one-eighth, one-fifth, one-fourth, onethird, and one-half the thickness of the PWB.
- 12. (Previously presented) The process of claim 1, wherein the first polymer is formed over the PWB by depositing a prepolymer selected from a resin, a cyanate ester, a polyimide, a polybenzoxazole, a polybenzimidazole, a polybenzothiazole, and combinations thereof, and wherein the first polymer includes a film-to-PWB thickness ratio selected from about one-tenth, one-eighth, one-fifth, one-fourth, one-third, and one-half the thickness of the PWB.

13. (Canceled)

14. (Previously presented) A process comprising:

first forming an imprinted first polymer disposed upon a PWB under conditions to increase the glass transition temperature (T_G) of the first polymer;

second forming an imprinted second polymer upon the imprinted first polymer to form a second topology including a second recess;

subsequently thermal curing the imprinted second polymer disposed over the first polymer, wherein subsequently thermal curing forms a cured polymer upper first film from the imprinted first polymer and a cured polymer upper second film from the imprinted second polymer, and

in situ testing a board layout on the PWB while attached as part of an array of PWBs.

15. (Previously Presented) The process of claim 14, wherein first forming forms a first recess, and wherein second forming forms a second recess, further including:

forming a first conductive material in the first recess; and

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forming a second conductive material in the second recess.

(Previously Presented) The process of claim 14 wherein first forming forms a first 16. recess, and wherein second forming forms a second recess, further including:

forming a first conductive material in the first recess, wherein forming a first conductive material is selected from blanket depositing and electroless plating; and after second curing

forming a second conductive material in the second recess, wherein forming a second conductive material is selected from blanket depositing and electroless plating.

- 17. (Previously presented) The process of claim 14, wherein the first polymer is formed over the PWB by depositing a prepolymer selected from a resin, a cyanate ester, a polyimide, a polybenzoxazole, a polybenzimidazole, a polybenzothiazole, and combinations thereof.
- 18. The process of claim 14, wherein the cured polymer first (Previously presented) film is in a film-to-PWB thickness ratio selected from about one-tenth, one-eighth, one-fifth, one-fourth, one-third, and one-half the thickness of the PWB.
- 19. The process of claim 14, wherein the first polymer is (Previously presented) formed over the PWB by depositing a prepolymer selected from a resin, a cyanate ester, a polyimide, a polybenzoxazole, a polybenzimidazole, a polybenzothiazole, and combinations thereof, and wherein the cured polymer first film is in a film-to-PWB thickness ratio selected from about one-tenth, one-eighth, one-fifth, one-fourth, one-third, and one-half the thickness of the PWB.
- 20. The process of claim 14, wherein subsequently thermal (Previously presented) curing is carried out under conditions to heat the first polymer at greater rate than the PWB.
- 21. (Withdrawn) A method comprising: assembling a die to a mounting substrate, wherein the mounting substrate includes:

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a first thermally imprinted cured polymer first film disposed upon a substrate; and a subsequently thermally imprinted cured polymer subsequent film disposed over the first cured polymer first film.

- 22. (Withdrawn) The method of claim 21, wherein assembling a die to a mounting substrate is selected from assembling a processor to a mother board, assembling a processor to a mezzanine board, assembling a processor to an expansion card, assembling a memory chip to a board, assembling a digital signal processor to a board, assembling a micro-controller to a board, assembling an application specific integrated circuit to a board, and combinations thereof.
- 23. (Withdrawn) The method of claim 21, wherein the cured polymer first film includes a first topology that exposes a portion of the substrate, wherein a first metallization is disposed within a recess in the first topology, wherein the cured polymer subsequent film includes a subsequent topology, wherein a subsequent metallization is disposed within a recess in the subsequent topology, the method further including:

forming an electrical bump in contact with the subsequent metallization; and coupling the electrical bump with the die.

24. (Withdrawn) The method of claim 21, wherein the first thermally imprinted polymer is imprinted under conditions to increase the glass transition temperature (T_G) of the first polymer, and wherein the subsequently thermally imprinted polymer is imprinted under conditions to increase the T_G of the subsequent polymer.

25-30. (Canceled).

31. (Previously presented) A process comprising:

first forming an imprinted first polymer disposed upon an array of printed wiring boards (PWBs) under conditions to increase the glass transition temperature (T_G) of the first polymer, wherein first forming an imprinted first polymer exposes a portion of the array of PWBs;

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subsequently thermal curing an imprinted subsequent polymer disposed over the first polymer, wherein subsequently thermal curing is carried out under conditions to heat the subsequent polymer at a greater rate than the array of PWBs; and

in situ testing the array of PWBs while not singulated.

- 32. (Previously Presented) The process of claim 31, wherein first forming achieves a first topology with a minimum feature within the first topology, and wherein the minimum feature exhibits a deviation from planarity of 10 percent or less.
- 33. (Previously presented) The process of claim 32, wherein the imprinted first polymer has in a film-to-PWB thickness ratio selected from about one-tenth, one-eighth, one-fifth, one-fourth, one-third, and one-half the thickness of the PWB.
- 34. (Currently amended) A process comprising:

first forming an imprinted first polymer disposed upon \underline{an} [[n]] array of printed wiring boards (PWBs) under conditions to increase the glass transition temperature (T_G) of the first polymer, wherein first forming forms a first recess;

forming a first conductive material in the first recess, wherein forming a first conductive material is selected from blanket depositing and electroless plating;

second forming an imprinted second polymer upon the imprinted first polymer to form a second topology including a second recess, wherein second forming forms a second recess;

forming a second conductive material in the second recess, wherein forming a second conductive material is selected from blanket depositing and electroless plating;

subsequently thermal curing the imprinted second polymer disposed over the first polymer, wherein subsequently thermal curing forms a cured polymer upper first film from the imprinted first polymer and a cured polymer upper second film from the imprinted second polymer, and wherein the cured polymer upper first film is in a film-to-substrate thickness ratio selected from about one-tenth, one-eighth, one-fifth, one-fourth, one-third, and one-half the thickness of the array of PWBs; and

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in situ testing a board layout on one PWB of the array of PWBs while not singulated from the array of substrates.

- 35. (Previously presented) The process of claim 34, wherein the first polymer is formed over the substrate by depositing a prepolymer selected from a resin, a cyanate ester, a polyimide, a polybenzoxazole, a polybenzimidazole, a polybenzothiazole, and combinations thereof and wherein subsequently thermal curing is carried out under conditions to heat the first polymer at greater rate than the array of PWBs.
- 36. (Previously presented) The process of claim 34, wherein subsequently thermal curing is carried out under conditions to heat the first polymer at greater rate than the array of PWBs, and wherein first forming achieves a first topology with a minimum feature within the first topology, and wherein the minimum feature exhibits a deviation from planarity of 10 percent or less.